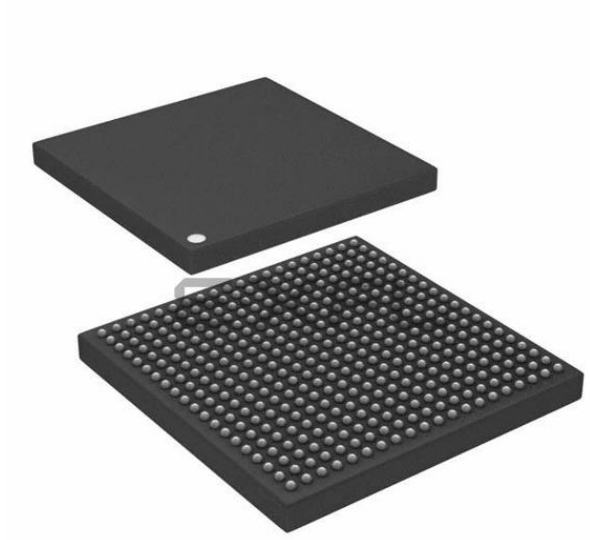

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Understanding Embedded - DSP (Digital Signal Processors)

Embedded - DSP (Digital Signal Processors) are specialized microprocessors designed to perform complex mathematical computations on digital signals in real-time. Unlike general-purpose processors, DSPs are optimized for high-speed numeric processing tasks, making them ideal for applications that require efficient and precise manipulation of digital data. These processors are fundamental in converting and processing signals in various forms, including audio, video, and communication signals, ensuring that data is accurately interpreted and utilized in embedded systems.

Applications of Embedded - DSP (Digital Signal Processors)

Details	
Product Status	Obsolete
Type	Fixed Point
Interface	Host Interface, I²C, UART
Clock Rate	266MHz
Non-Volatile Memory	ROM (8kB)
On-Chip RAM	400kB
Voltage - I/O	3.30V
Voltage - Core	1.20V
Operating Temperature	-40°C ~ 105°C (TJ)
Mounting Type	Surface Mount
Package / Case	400-LFBGA
Supplier Device Package	400-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmsc7116vm1000

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1.2 Signal List By Ball Location

Table 1 lists the signals sorted by ball number and configuration.

Table 1. MSC7116 Signals by Ball Designator

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
A1	GND					
A2	GND					
A3	DQM1					
A4	DQS2					
A5	CK					
A6	$\overline{CK}$					
A7	GPIC7			GPOC7	HD15	
A8	GPIC4			GPOC4	HD12	
A9	GPIC2			GPOC2	HD10	
A10	reserved				HD7	
A11	reserved				HD6	
A12	reserved				HD4	
A13	reserved				HD1	
A14	reserved				HD0	
A15	GND					
A16	BM3	GPID8		GPOD8	reserved	
A17	NC					
A18	NC					
A19	NC					
A20	NC					
B1	V_{DDM}					
B2	NC					
B3	$\overline{CS0}$					
B4	DQM2					
B5	DQS3					
B6	DQS0					
B7	CKE					
B8	$\overline{WE}$					
B9	GPIC6			GPOC6	HD14	
B10	GPIC3			GPOC3	HD11	
B11	GPIC0			GPOC0	HD8	
B12	reserved				HD5	
B13	reserved				HD2	

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
B14	NC					
B15	BM2	GPID7		GPOD7	reserved	
B16	NC					
B17	NC					
B18	NC					
B19	NC					
B20	NC					
C1	D24					
C2	D30					
C3	D25					
C4	$\overline{CS1}$					
C5	DQM3					
C6	DQM0					
C7	DQS1					
C8	$\overline{RAS}$					
C9	$\overline{CAS}$					
C10	GPIC5			GPOC5	HD13	
C11	GPIC1			GPOC1	HD9	
C12	reserved				HD3	
C13	NC					
C14	NC					
C15	NC					
C16	NC					
C17	NC					
C18	NC					
C19	NC					
C20	NC					
D1	V_{DDM}					
D2	D28					
D3	D27					
D4	GND					
D5	V_{DDM}					
D6	V_{DDM}					
D7	V_{DDM}					
D8	V_{DDM}					
D9	V_{DDM}					

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
H2	D12					
H3	D11					
H4	V_{DDM}					
H5	V_{DDM}					
H6	GND					
H7	GND					
H8	GND					
H9	GND					
H10	GND					
H11	GND					
H12	GND					
H13	GND					
H14	GND					
H15	V_{DDIO}					
H16	V_{DDIO}					
H17	V_{DDC}					
H18	NC					
H19	reserved				HA2	
H20	reserved				HA1	
J1	D10					
J2	V_{DDM}					
J3	D9					
J4	V_{DDM}					
J5	V_{DDM}					
J6	V_{DDM}					
J7	GND					
J8	GND					
J9	GND					
J10	GND					
J11	GND					
J12	GND					
J13	GND					
J14	GND					
J15	GND					
J16	V_{DDIO}					
J17	V_{DDC}					

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
N10	GND					
N11	GND					
N12	GND					
N13	GND					
N14	GND					
N15	V_{DDIO}					
N16	V_{DDC}					
N17	V_{DDC}					
N18	CLKIN					
N19	GPIA15		$\overline{IRQ14}$	GPOA15	SCL	
N20	V_{SSPLL}					
P1	D7					
P2	D17					
P3	D16					
P4	V_{DDM}					
P5	V_{DDM}					
P6	V_{DDM}					
P7	GND					
P8	GND					
P9	GND					
P10	GND					
P11	GND					
P12	GND					
P13	GND					
P14	GND					
P15	V_{DDIO}					
P16	V_{DDIO}					
P17	V_{DDC}					
P18	$\overline{PORESET}$					
P19	TPSEL					
P20	V_{DDPLL}					
R1	GND					
R2	D19					
R3	D18					
R4	V_{DDM}					
R5	V_{DDM}					

Table 1. MSC7116 Signals by Ball Designator (continued)

Number	Signal Names					
	End of Reset	Software Controlled			Hardware Controlled	
		GPI Enabled (Default)	Interrupt Enabled	GPO Enabled	Primary	Alternate
R6	V_{DDM}					
R7	GND					
R8	V_{DDM}					
R9	GND					
R10	V_{DDM}					
R11	GND					
R12	GND					
R13	V_{DDIO}					
R14	GND					
R15	V_{DDIO}					
R16	V_{DDIO}					
R17	V_{DDC}					
R18	TDO					
R19	reserved				EE0/DBREQ	
R20	TEST0					
T1	V_{DDM}					
T2	D20					
T3	D22					
T4	V_{DDM}					
T5	V_{DDM}					
T6	V_{DDC}					
T7	V_{DDM}					
T8	V_{DDM}					
T9	V_{DDC}					
T10	V_{DDM}					
T11	V_{DDM}					
T12	V_{DDIO}					
T13	V_{DDIO}					
T14	V_{DDIO}					
T15	V_{DDIO}					
T16	V_{DDC}					
T17	V_{DDC}					
T18	reserved				MDIO	
T19	TMS					
T20	$\overline{\text{HRESET}}$					
U1	GND					

Table 5. DC Electrical Characteristics (continued)

Characteristic	Symbol	Min	Typical	Max	Unit
Tri-state (high impedance off state) leakage current, $V_{IN} = V_{DDIO}$	I_{OZ}	–1.0	0.09	1	µA
Signal low input current, V_{IL} = 0.4 V	I_L	–1.0	0.09	1	µA
Signal high input current, V_{IH} = 2.0 V	I_H	–1.0	0.09	1	µA
Output high voltage, I_{OH} = –2 mA, except open drain pins	V_{OH}	2.0	3.0	—	V
Output low voltage, I_{OL}= 5 mA	V_{OL}	—	0	0.4	V
Typical power at 266 MHz[5]	P	—	293.0	—	mW

Notes:
1. The value of V_{DDM} at the MSC7116 device must remain within 50 mV of V_{DDM} at the DRAM device at all times.
2. V_{REF} must be equal to 50% of V_{DDM} and track V_{DDM} variations as measured at the receiver. Peak-to-peak noise must not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the MSC7116 device. It is the level measured at the far end signal termination. It should be equal to V_{REF}. This rail should track variations in the DC level of V_{REF}.
4. Output leakage for the memory interface is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ V_{DDM}.
5. The core power values were measured.using a standard EFR pattern at typical conditions (25°C, 300 MHz, 1.2 V core).

Table 6 lists the DDR DRAM capacitance.

Table 6. DDR DRAM Capacitance

Parameter/Condition	Symbol	Max	Unit
Input/output capacitance: DQ, DQS	C_{IO}	30	pF
Delta input/output capacitance: DQ, DQS	C_{DIO}	30	pF

Note: These values were measured under the following conditions:
- V_{DDM} = 2.5 V ± 0.125 V
- f = 1 MHz
- T_A = 25°C
- $V_{OUT} = V_{DDM}/2$
- V_{OUT} (peak to peak) = 0.2 V

2.5 AC Timings

This section presents timing diagrams and specifications for individual signals and parallel I/O outputs and inputs. All AC timings are based on a 30 pF load, except where noted otherwise, and a 50 Ω transmission line. For any additional pF, use the following equations to compute the delay:

— Standard interface: 2.45 + (0.054 × C_{load}) ns

— DDR interface: 1.6 + (0.002 × C_{load}) ns

2.5.1 Clock and Timing Signals

The following tables describe clock signal characteristics. **Table 6** shows the maximum frequency values for internal (core, reference, and peripherals) and external (CLKO) clocks. You must ensure that maximum frequency values are not exceeded (see **Section 2.5.2** for the allowable ranges when using the PLL).

Table 6. Maximum Frequencies

Characteristic	Maximum in MHz
Core clock frequency (CLOCK)	266
External output clock frequency (CLKO)	67
Memory clock frequency (CK, $\overline{CK}$)	133
TDM clock frequency (TxRCK, TxTCK)	50

Table 7. Clock Frequencies in MHz

Characteristic	Symbol	Min	Max
CLKIN frequency	F_{CLKIN}	10	100
CLOCK frequency	F_{CORE}	—	266
CK, $\overline{CK}$ frequency	F_{CK}	—	133
TDMxRCK, TDMxTCK frequency	F_{TDMCK}	—	50
CLKO frequency	F_{CKO}	—	67
AHB/IPBus/APB clock frequency	F_{BCK}	—	133
Note: The rise and fall time of external clocks should be 5 ns maximum			

Table 8. System Clock Parameters

Characteristic	Min	Max	Unit
CLKIN frequency	10	100	MHz
CLKIN slope	—	5	ns
CLKIN frequency jitter (peak-to-peak)	—	1000	ps
CLKO frequency jitter (peak-to-peak)	—	133	ps

2.5.3.2 Reset Configuration

The MSC7116 has two mechanisms for writing the reset configuration:

- From a host through the host interface (HDI16)
- From memory through the I^2C interface

Five signal levels (see **Chapter 1** for signal description details) are sampled on $\overline{\text{PORESET}}$ deassertion to define the boot and operating conditions:

- BM[0–1]
- SWTE
- H8BIT
- HDSP

2.5.3.3 Reset Timing Tables

Table 16 and **Figure 4** describe the reset timing for a reset configuration write.

Table 16. Timing for a Reset Configuration Write

No.	Characteristics	Expression	Unit
1	Required external $\overline{\text{PORESET}}$ duration minimum	$16/F_{CLKIN}$	clocks
2	Delay from $\overline{\text{PORESET}}$ deassertion to $\overline{\text{HRESET}}$ deassertion	$521/F_{CLKIN}$	clocks
Note:	Timings are not tested, but are guaranteed by design.		

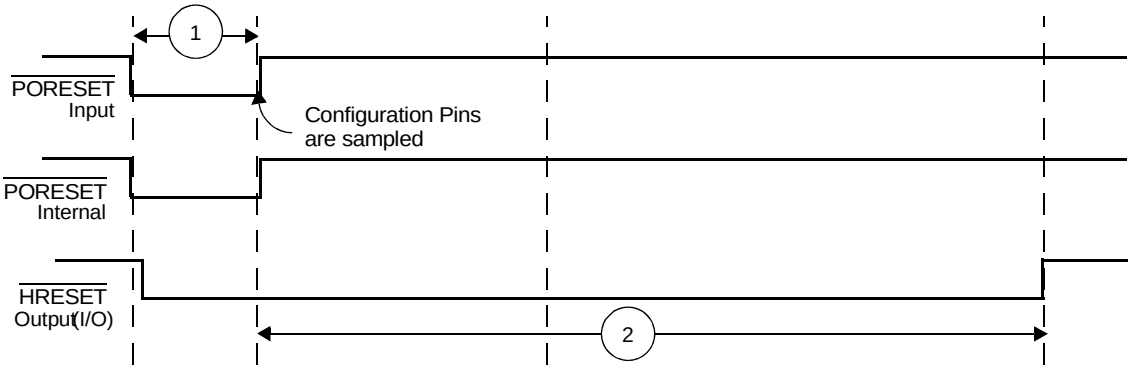


Figure 4. Timing Diagram for a Reset Configuration Write

2.5.4 DDR DRAM Controller Timing

This section provides the AC electrical characteristics for the DDR DRAM interface.

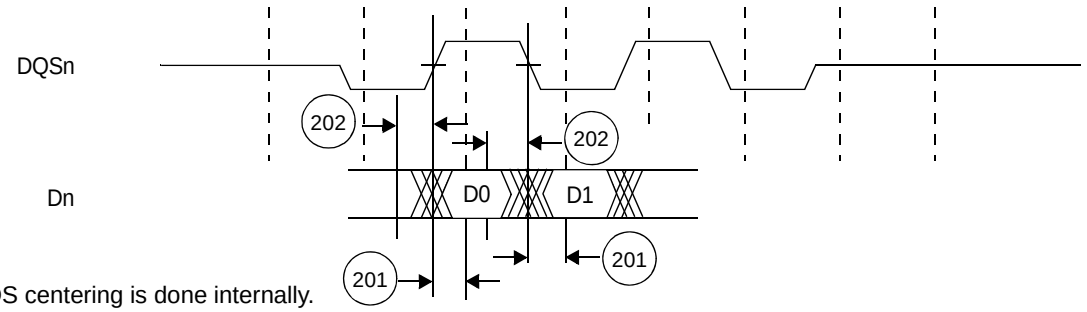
2.5.4.1 DDR DRAM Input AC Timing Specifications

Table 17 provides the input AC timing specifications for the DDR DRAM interface.

Table 17. DDR DRAM Input AC Timing

No.	Parameter	Symbol	Min	Max	Unit
—	AC input low voltage	V_{IL}	—	V_{REF} – 0.31	V
—	AC input high voltage	V_{IH}	V_{REF} + 0.31	V_{DDM} + 0.3	V
201	Maximum Dn input setup skew relative to DQSn input	—	—	900	ps
202	Maximum Dn input hold skew relative to DQSn input	—	—	900	ps

Notes:
1. Maximum possible skew between a data strobe (DQSn) and any corresponding bit of data (D[8n + {0...7}] if 0 ≤ n ≤ 7).
2. See **Table 18** for t_{CK} value.
3. Dn should be driven at the same time as DQSn. This is necessary because the DQSn centering on the DQn data tenure is done internally.



Note: DQS centering is done internally.

Figure 5. DDR DRAM Input Timing Diagram

2.5.4.2 DDR DRAM Output AC Timing Specifications

Table 18 and **Table 19** list the output AC timing specifications and measurement conditions for the DDR DRAM interface.

Table 18. DDR DRAM Output AC Timing

No.	Parameter	Symbol	Min	Max	Unit
200	CK cycle time, (CK/$\overline{CK}$ crossing)[1] • 100 MHz (DDR200) • 150 MHz (DDR300)	t_{CK}	 10 6.67	 — —	 ns ns
204	An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE output setup with respect to CK	t_{DDKHAS}	$0.5 \times t_{CK} - 1000$	—	ps
205	An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE output hold with respect to CK	t_{DDKHAX}	$0.5 \times t_{CK} - 1000$	—	ps
206	$\overline{CSn}$ output setup with respect to CK	t_{DDKHCS}	$0.5 \times t_{CK} - 1000$	—	ps
207	$\overline{CSn}$ output hold with respect to CK	t_{DDKHCX}	$0.5 \times t_{CK} - 1000$	—	ps
208	CK to DQSn[2]	t_{DDKHMH}	–600	600	ps

Table 18. DDR DRAM Output AC Timing (continued)

No.	Parameter	Symbol	Min	Max	Unit
209	Dn/DQMn output setup with respect to DQSn[3]	t_{DDKHDS}, t_{DDKLDS}	$0.25 \times t_{CK} - 750$	—	ps
210	Dn/DQMn output hold with respect to DQSn[3]	t_{DDKHDX}, t_{DDKLDX}	$0.25 \times t_{CK} - 750$	—	ps
211	DQSn preamble start[4]	t_{DDKHMP}	$-0.25 \times t_{CK}$	—	ps
212	DQSn epilogue end[5]	t_{DDKHME}	–600	600	ps

Notes:
1. All CK/$\overline{CK}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
2. t_{DDKHMH} can be modified through the TCFG2[WRDD] DQSS override bits. The DRAM requires that the first write data strobe arrives 75–125% of a DRAM cycle after the write command is issued. Any skew between DQSn and CK must be considered when trying to achieve this 75%–125% goal. The TCFG2[WRDD] bits can be used to shift DQSn by 1/4 DRAM cycle increments. The skew in this case refers to an internal skew existing at the signal connections. By default, the CK/$\overline{CK}$ crossing occurs in the middle of the control signal (An/$\overline{RAS}$/$\overline{CAS}$/$\overline{WE}$/CKE) tenure. Setting TCFG2[ACSM] bit shifts the control signal assertion 1/2 DRAM cycle earlier than the default timing. This means that the signal is asserted no earlier than 600 ps before the CK/$\overline{CK}$ crossing and no later than 600 ps after the crossing time; the device uses 1200 ps of the skew budget (the interval from –600 to +600 ps). Timing is verified by referencing the falling edge of CK. See Chapter 10 of the *MSC711x Reference Manual* for details.
3. Determined by maximum possible skew between a data strobe (DQS) and any corresponding bit of data. The data strobe should be centered inside of the data eye.
4. Please note that this spec is in reference to the DQSn first rising edge. It could also be referenced from CK(r), but due to programmable delay of the write strobes (TCFG2[WRDD]), there pre-amble may be extended for a full DRAM cycle. For this reason, we reference from DQSn.
5. All outputs are referenced to the rising edge of CK. Note that this is essentially the CK/DQSn skew in spec 208. In addition there is no real “maximum” time for the epilogue end. JEDEC does not require this is as a device limitation, but simply for the chip to guarantee fast enough write-to-read turn-around times. This is already guaranteed by the memory controller operation.

Figure 6 shows the DDR DRAM output timing diagram.

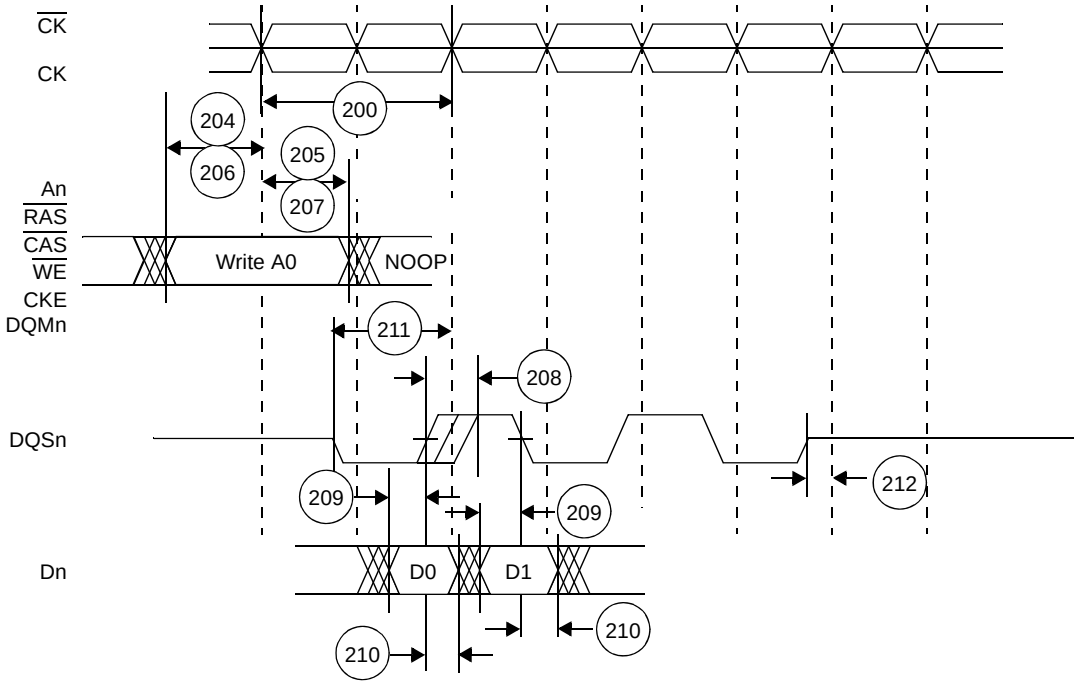


Figure 6. DDR DRAM Output Timing Diagram

2.5.6.2 Transmit Signal Timing

Table 22. Transmit Signal Timing

No.	Characteristics	Min	Max	Unit
800	Transmit clock period: • MII: TXCLK • RMII: REFCLK	 40 20	 — —	 ns ns
801	Transmit clock pulse width high—as a percent of clock period • MII: RXCLK • RMII: REFCLK	35 14 7	65 — —	% ns ns
802	Transmit clock pulse width low—as a percent of clock period: • MII: RXCLK • RMII: REFCLK	35 14 7	65 — —	% ns ns
805	Transmit clock to TXDn, TX_EN, TX_ER invalid	4	—	ns
806	Transmit clock to TXDn, TX_EN, TX_ER valid	—	14	ns

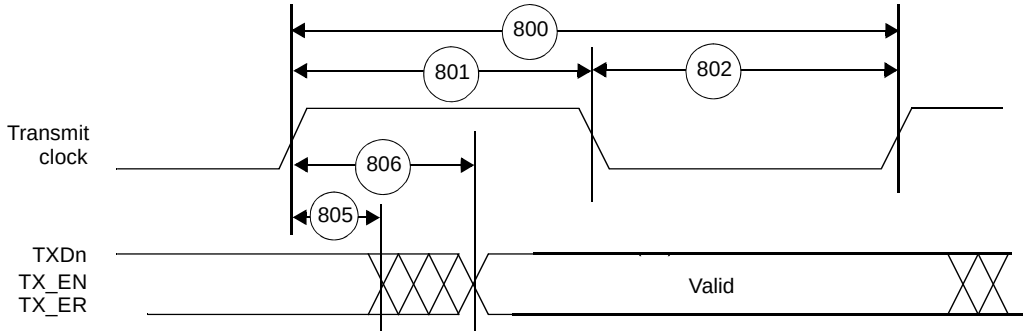


Figure 11. Ethernet Receive Signal Timing

2.5.6.3 Asynchronous Input Signal Timing

Table 23. Asynchronous Input Signal Timing

No.	Characteristics	Min	Max	Unit
807	• MII: CRS and COL minimum pulse width (1.5 × TXCLK period) • RMII: CRS_DV minimum pulse width (1.5 x REFCLK period)	60 30	— —	ns ns

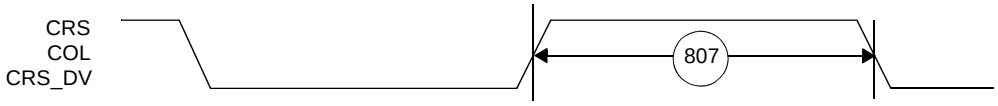


Figure 12. Asynchronous Input Signal Timing

2.5.13 JTAG Signals

Table 31. JTAG Timing

No.	Characteristics	All frequencies		Unit
		Min	Max	
700	TCK frequency of operation (1/($T_C \times 3$) **Note:** T_C = 1/CLOCK which is the period of the core clock. The TCK frequency must less than 1/3 of the core frequency with an absolute maximum limit of 40 MHz.	0.0	40.0	MHz
701	TCK cycle time	25.0	—	ns
702	TCK clock pulse width measured at V_M = 1.6 V	11.0	—	ns
703	TCK rise and fall times	0.0	3.0	ns
704	Boundary scan input data set-up time	5.0	—	ns
705	Boundary scan input data hold time	14.0	—	ns
706	TCK low to output data valid	0.0	20.0	ns
707	TCK low to output high impedance	0.0	20.0	ns
708	TMS, TDI data set-up time	5.0	—	ns
709	TMS, TDI data hold time	14.0	—	ns
710	TCK low to TDO data valid	0.0	24.0	ns
711	TCK low to TDO high impedance	0.0	10.0	ns
712	$\overline{\text{TRST}}$ assert time	100.0	—	ns
Note:	All timings apply to OCE module data transfers as the OCE module uses the JTAG port as an interface.			

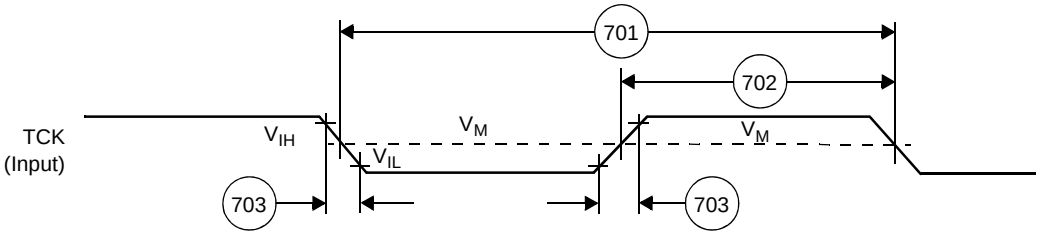


Figure 26. Test Clock Input Timing Diagram

3.2 Power Supply Design Considerations

This section outlines the MSC7116 power considerations: power supply, power sequencing, power planes, decoupling, power supply filtering, and power consumption. It also presents a recommended power supply design and options for low-power consumption. For information on AC/DC electrical specifications and thermal characteristics, refer to **Section 2**.

3.2.1 Power Supply

The MSC7116 requires four input voltages, as shown in **Table 32**.

Table 32. MSC7116 Voltages

Voltage	Symbol	Value
Core	V_{DDC}	1.2 V
Memory	V_{DDM}	2.5 V
Reference	V_{REF}	1.25 V
I/O	V_{DDIO}	3.3 V

You should supply the MSC7116 core voltage via a variable switching supply or regulator to allow for compatibility with possible core voltage changes on future silicon revisions. The core voltage is supplied with 1.2 V (+5% and –10%) across V_{DDC} and GND and the I/O section is supplied with 3.3 V (± 10%) across V_{DDIO} and GND. The memory and reference voltages supply the DDR memory controller block. The memory voltage is supplied with 2.5 V across V_{DDM} and GND. The reference voltage is supplied across V_{REF} and GND and must be between $0.49 \times V_{DDM}$ and $0.51 \times V_{DDM}$. Refer to the JEDEC standard JESD8 (*Stub Series Terminated Logic for 2.5 Volts* (STTL_2)) for memory voltage supply requirements.

3.2.2 Power Sequencing

One consequence of multiple power supplies is that the voltage rails ramp up at different rates when power is initially applied. The rates depend on the power supply, the type of load on each power supply, and the way different voltages are derived. It is extremely important to observe the power up and power down sequences at the board level to avoid latch-up, forward biasing of ESD devices, and excessive currents, which all lead to severe device damage.

Note: There are five possible power-up/power-down sequence cases. The first four cases listed in the following sections are recommended for new designs. The fifth case is not recommended for new designs and must be carefully evaluated for current spike risks based on actual information for the specific application.

3.2.2.4 Case 4

The power-up sequence is as follows:

1. Turn on the V_{DDIO} (3.3 V) supply first.
2. Turn on the V_{DDC} (1.2 V), V_{DDM} (2.5 V), and V_{REF} (1.25 V) supplies simultaneously (second).

Note: Make sure that the time interval between the ramp-up of V_{DDIO} and V_{DDC} is less than 10 ms.

The power-down sequence is as follows:

1. Turn off the V_{DDC} (1.2 V), V_{REF} (1.25 V), and V_{DDM} (2.5 V) supplies simultaneously (first).
2. Turn of the V_{DDIO} (3.3 V) supply last.

Use the following guidelines:

- Make sure that the time interval between the ramp-up or ramp-down time for V_{DDC} and V_{DDM} is less than 10 ms for power-up and power-down.
- Refer to **Figure 33** for relative timing for Case 4.

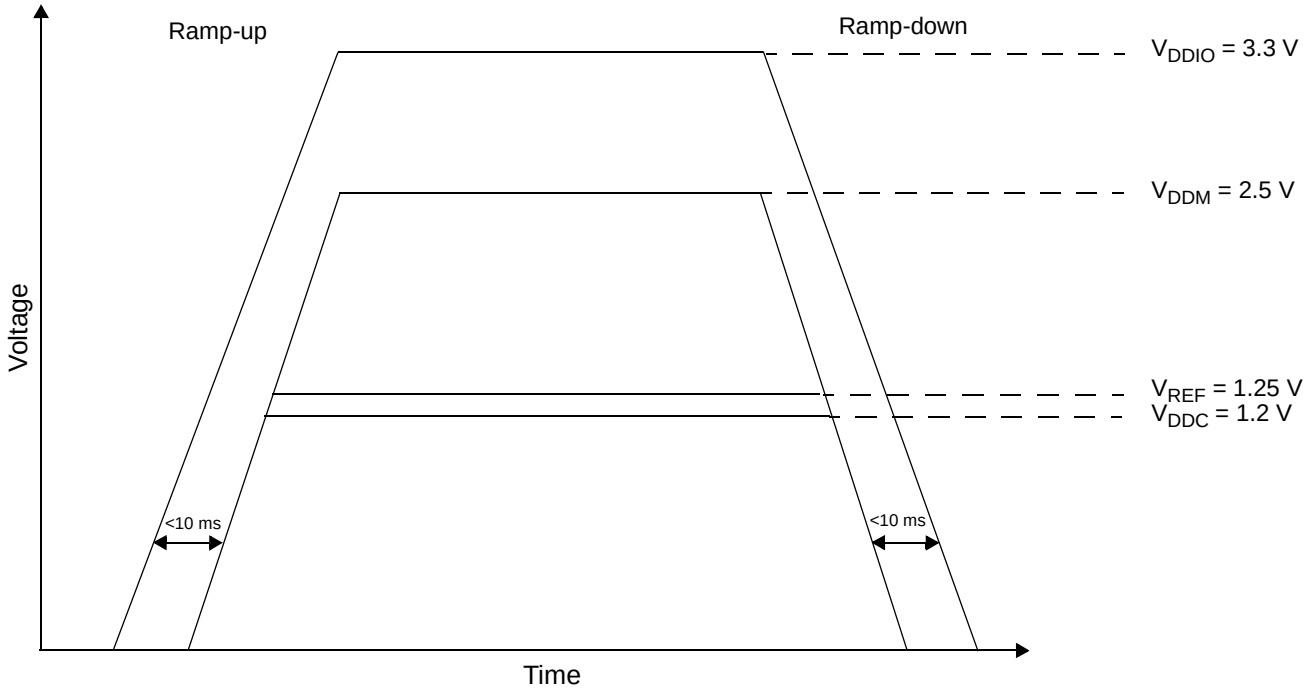


Figure 33. Voltage Sequencing Case 4

3.2.3 Power Planes

Each power supply pin (V_{DDC}, $V_{DDM,}$ and V_{DDIO}) should have a low-impedance path to the board power supply. Each GND pin should be provided with a low-impedance path to ground. The power supply pins drive distinct groups of logic on the device. The MSC7116 V_{DDC} power supply pins should be bypassed to ground using decoupling capacitors. The capacitor leads and associated printed circuit traces connecting to device power pins and GND should be kept to less than half an inch per capacitor lead. A minimum four-layer board that employs two inner layers as power and GND planes is recommended. See **Section 3.5** for DDR Controller power guidelines.

3.2.4 Decoupling

Both the I/O voltage and core voltage should be decoupled for switching noise. For I/O decoupling, use standard capacitor values of 0.01 µF for every two to three voltage pins. For core voltage decoupling, use two levels of decoupling. The first level should consist of a 0.01 µF high frequency capacitor with low effective series resistance (ESR) and effective series inductance (ESL) for every two to three voltage pins. The second decoupling level should consist of two bulk/tantalum decoupling capacitors, one 10 µF and one 47 µF, (with low ESR and ESL) mounted as closely as possible to the MSC7116 voltage pins. Additionally, the maximum drop between the power supply and the DSP device should be 15 mV at 1 A.

3.2.5 PLL Power Supply Filtering

The MSC7116 V_{DDPLL} power signal provides power to the clock generation PLL. To ensure stability of the internal clock, the power supplied to this pin should be filtered with capacitors that have low and high frequency filtering characteristics. V_{DDPLL} can be connected to V_{DDC} through a 2 Ω resistor. V_{SSPLL} can be tied directly to the GND plane. A circuit similar to the one shown in **Figure 35** is recommended. The PLL loop filter should be placed as closely as possible to the V_{DDPLL} pin (which are located on the outside edge of the silicon package) to minimize noise coupled from nearby circuits.The 0.01 µF capacitor should be closest to V_{DDPLL}, followed by the 0.1 µF capacitor, the 10 µF capacitor, and finally the 2-Ω resistor to V_{DDC}. These traces should be kept short.

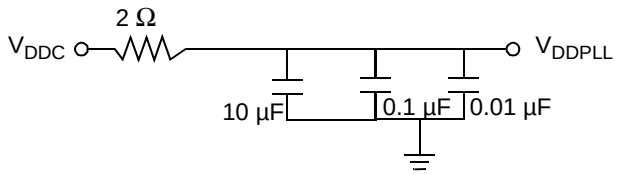


Figure 35. PLL Power Supply Filter Circuits

3.2.6 Power Consumption

You can reduce power consumption in your design by controlling the power consumption of the following regions of the device:

- *Extended core.* Use the SC1400 Stop and Wait modes by issuing a **stop** or **wait** instruction.
- *Clock synthesis module.* Disable the PLL, timer, watchdog, or DDR clocks or disable the CLKO pin.
- *AHB subsystem.* Freeze or shut down the AHB subsystem using the GPSCTL[XBR_HRQ] bit.
- *Peripheral subsystem.* Halt the individual on-device peripherals such as the DDR memory controller, Ethernet MAC, HDI16, TDM, UART, I^2C, and timer modules.

For details, see the “Clocks and Power Management” chapter of the *MSC711x Reference Manual*.

3.2.7 Power Supply Design

One of the most common ways to derive power is to use either a simple fixed or adjustable linear regulator. For the system I/O voltage supply, a simple fixed 3.3 V supply can be used. However, a separate adjustable linear regulator supply for the core voltage V_{DDC} should be implemented. For the memory power supply, regulators are available that take care of all DDR power requirements.

Table 33. Recommended Power Supply Ratings

Supply	Symbol	Nominal Voltage	Current Rating
Core	V_{DDC}	1.2 V	1.5 A per device
Memory	V_{DDM}	2.5 V	0.5 A per device
Reference	V_{REF}	1.25 V	10 µA per device
I/O	V_{DDIO}	3.3 V	1.0 A per device

3.3 Estimated Power Usage Calculations

The following equations permit estimated power usage to be calculated for individual design conditions. Overall power is derived by totaling the power used by each of the major subsystems:

$$P_{TOTAL} = P_{CORE} + P_{PERIPHERALS} + P_{DDRIO} + P_{IO} + P_{LEAKAGE} \quad \textit{Eqn. 3}$$

This equation combines dynamic and static power. Dynamic power is determined using the generic equation:

$$C \times V^2 \times F \times 10^{-3}\ mW \quad \textit{Eqn. 4}$$

where,

C = load capacitance in pF

V = peak-to-peak voltage swing in V

F = frequency in MHz

3.3.1 Core Power

Estimation of core power is straightforward. It uses the generic dynamic power equation and assumes that the core load capacitance is 750 pF, core voltage swing is 1.2 V, and the core frequency is 266 MHz. This yields:

$$P_{CORE} = 750\ pF \times (1.2\ V)^2 \times 266\ MHz \times 10^{-3} = 287\ mW \quad \textit{Eqn. 5}$$

This equation allows for adjustments to voltage and frequency if necessary.

When booting from a power-on reset, the HDI16 is additionally configurable as follows:

- 8- or 16-bit mode as specified by the H8BIT pin.
- Data strobe as specified by the HDSP and HDDS pins.

These pins are sampled only on the deassertion of power-on reset. During a boot from a hard reset, the configuration of these pins is unaffected.

Note: When the HDI16 is used for booting or other purposes, bit 0 is the least significant bit and not the most significant bit as for other DSP products.

3.4.3.2 I^2C Boot

When the MSC7116 device is configured to boot from the I^2C port, the boot program configures the GPIO pins for I^2C operation. Then the MSC7116 device initiates accesses to the I^2C module, downloading data to the MSC7116 device. The I^2C interface is configured as follows:

- PLL is disabled and bypassed so that the I^2C module is clocked with the IPBus clock.
- I^2C interface operates in master mode and polling is used.
- EPROM operates in slave mode.
- Clock divider is set to 128.
- Address of slave during boot is 0xA0.

The IPBus clock is internally divided to generate the bit clock, as follows:

- CLKIN must be a maximum of 100 MHz
- PLL is bypassed.
- IPBus clock = CLKIN/2 is a maximum of 50 MHz.
- I^2C bit clock must be less than or equal to:
  - IPBus clock/I^2C clock divider
  - 50 MHz (max)/128
  - 390.6 KHz

This satisfies the maximum clock rate requirement of 400 kbps for the I^2C interface. For details on the boot procedure, see the "Boot Program" chapter of the *MSC711x Reference Manual*.

3.4.3.3 SPI Boot

When the MSC7116 device is configured to boot from the SPI port, the boot program configures the GPIO pins for SPI operation. Then the MSC7116 device initiates accesses to the SPI module, downloading data to the MSC7116 device. When the SPI routines run in the boot ROM, the MSC7116 is always configured as the SPI master. Booting through the SPI is supported for serial EEPROM devices and serial Flash devices. When a READ_ID instruction is issued to the serial memory device and the device returns a value of 0x00 or 0xFF, the routines for accessing a serial EEPROM are used, at a maximum frequency of 4 Mbps. Otherwise, the routines for accessing a serial Flash are used, and they can run at faster speeds. Booting is performed through one of two sets of pins:

- Main set: BM[2–3], HA3, and HCS2, which allow use of the PLL.
- Alternate set: UTXD, URXD, SDA, and SCL, which cannot be used with the PLL.

In either configuration, an error during SPI boot is flagged on the EVNT3 pin. For details on the boot procedure, see the "Boot Program" chapter of the *MSC711x Reference Manual*.

3.5 DDR Memory System Guidelines

MSC7116 devices contain a memory controller that provides a glueless interface to external double data rate (DDR) SDRAM memory modules with Class 2 Series Stub Termination Logic 2.5 V (SSTL_2). There are two termination techniques, as shown in Figure 36. Technique B is the most popular termination technique.

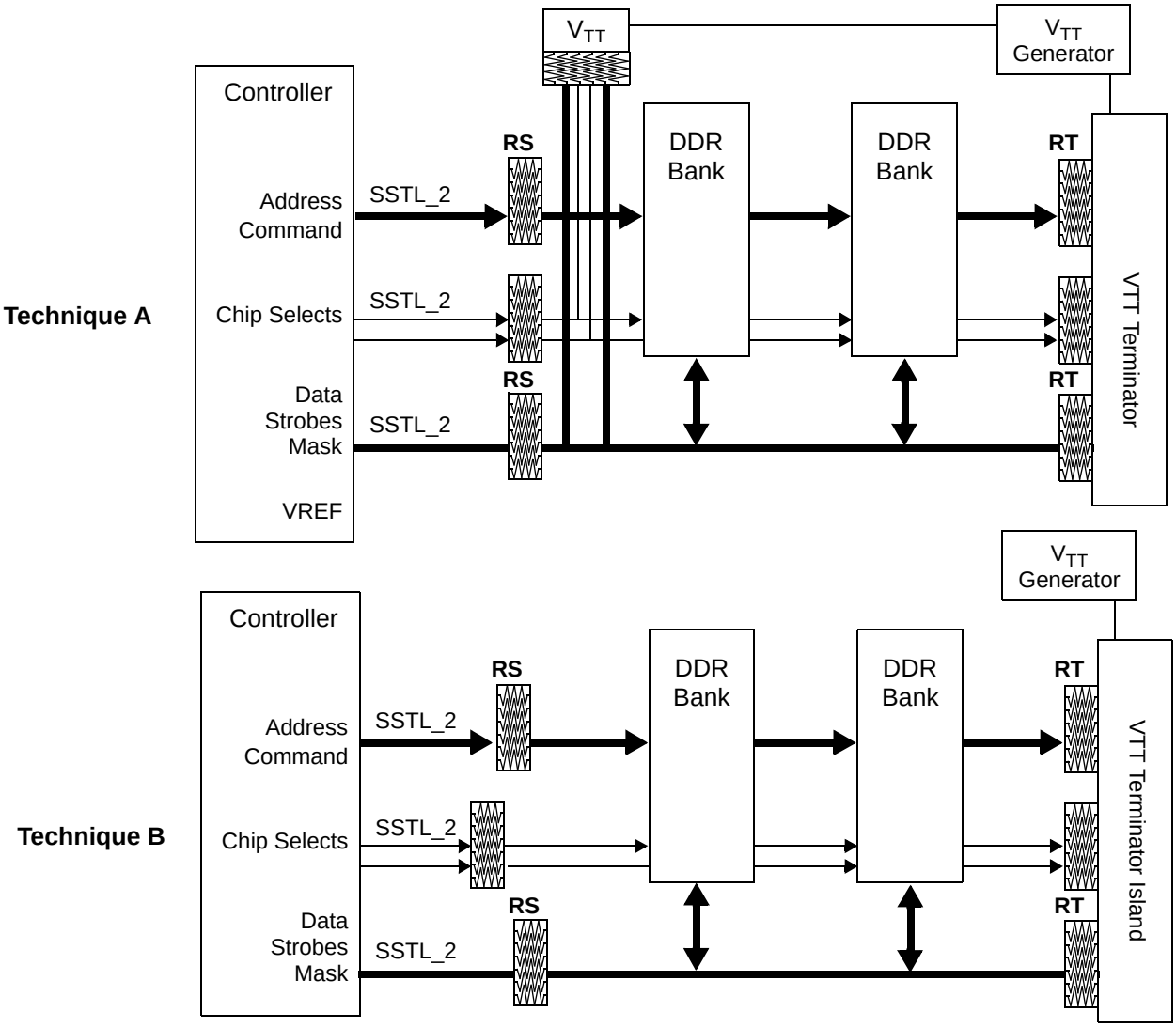


Figure 36. SSTL Termination Techniques

Figure 37 illustrates the power wattage for the resistors. Typical values for the resistors are as follows:

- RS = 22 Ω
- RT = 24 Ω

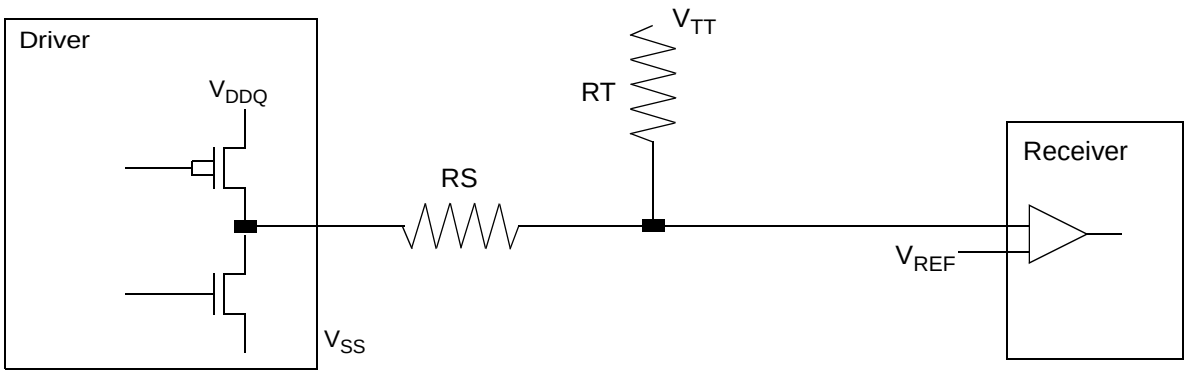


Figure 37. SSTL Power Value

3.5.1 V_{REF} and V_{TT} Design Constraints

V_{TT} and V_{REF} are isolated power supplies at the same voltage, with V_{TT} as a high current power source. This section outlines the voltage supply design needs and goals:

- Minimize the noise on both rails.
- V_{TT} must track variation in the V_{REF} DC offsets. Although they are isolated supplies, one possible solution is to use a single IC to generate both signals.
- Both references should have minimal drift over temperature and source supply.
- It is important to minimize the noise from coupling onto V_{REF} as follows:
  - Isolate V_{REF} and shield it with a ground trace.
  - Use 15–20 mm track.
  - Use 20–30 mm clearance between other traces for isolating.
  - Use the outer layer route when possible.
  - Use distributed decoupling to localize transient currents and return path and decouple with an inductance less than 3 nH.
- Max source/sink transient currents of up to 1.8 A for a 32-bit data bus.
- Use a wide island trace on the outer layer:
  - Place the island at the end of the bus.
  - Decouple both ends of the bus.
  - Use distributed decoupling across the island.
  - Place SSTL termination resistors inside the V_{TT} island and ensure a good, solid connection.
- Place the V_{TT} regulator as closely as possible to the termination island.
  - Reduce inductance and return path.
  - Tie current sense pin at the midpoint of the island.

3.5.2 Decoupling

The DDR decoupling considerations are as follows:

- DDR memory requires significantly more burst current than previous SDRAMs.
- In the worst case, up to 64 drivers may be switching states.
- Pay special attention and decouple discrete ICs per manufacturer guidelines.
- Leverage V_{TT} island topology to minimize the number of capacitors required to supply the burst current needs of the termination rail.
- See the Micron DesignLine publication entitled *Decoupling Capacitor Calculation for a DDR Memory Channel* (`http://download.micron.com/pdf/pubs/designline/3Q00dl1-4.pdf`).